
State-of-the-Art Program on Compound Semiconductors 45 (SOTAPOCS 45) -and- Wide Bandgap Semiconductor Materials and Devices 7

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PREFACE

The forty-fifth State-of-the-Art Program on Compound Semiconductors (SOTAPOCS XXXXV) and the seventh Symposium on Wide Bandgap Semiconductor Materials and Devices (Wide Bandgap VII) will be held at the 210th Meeting of The Electrochemical Society, Inc., October 29-November 3, 2006 in Cancun Mexico. Both symposia are sponsored by the Electronics Division of The Electrochemical Society.

The combined program will consist of four half-day sessions with subject areas covering material preparation of III-Nitride and other III-V semiconductors, material and device processing and characterization, novel optoelectronic and electronic devices and their applications. A total of 60 papers will be presented including invited papers by T.J. Anderson, J.D. Brown, J. Campbell, L.C. Chen, D.K. Choi, M. W. Cole, A. Dabiran, M. D'Evelyn, C. Eddy, N. Gardner, B. Gila, P. Holloway, C. Jagadish, P. Klein, H. Kuo, C. D. Lee, J. Lin, Y. Lu, J. Mittereder, S. Mahoney, P. Shen, R.J. Shul, J. Smart, C.W.Tu, J. Tucker and J. Zavada.

This issue of *ECS Transactions* continues the SOTAPOCS tradition of being published before the meeting. It includes 51 of the 60 papers to be presented. The texts of the remaining papers are unavailable from the authors in time for publication of this volume. The papers are arranged in the order of presentation scheduled at the meeting. Invited papers are denoted by an asterisk in the table of contents.

The editors gratefully acknowledge the authors for their efforts to submit the manuscripts in time, enabling this proceedings volume to be published before the meeting. We thank the organizers, the speakers, especially the invited speakers, and the session chairpersons for their contributions to the success of the symposia. A list of the organizers of both symposia is shown on page iv. The financial support of the Electronics Division is also gratefully acknowledged. Finally, we wish to express our appreciation to the staff of The Electrochemical Society for their cooperation and efforts to publish this volume on a very tight schedule.

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